HFZT

BC856S

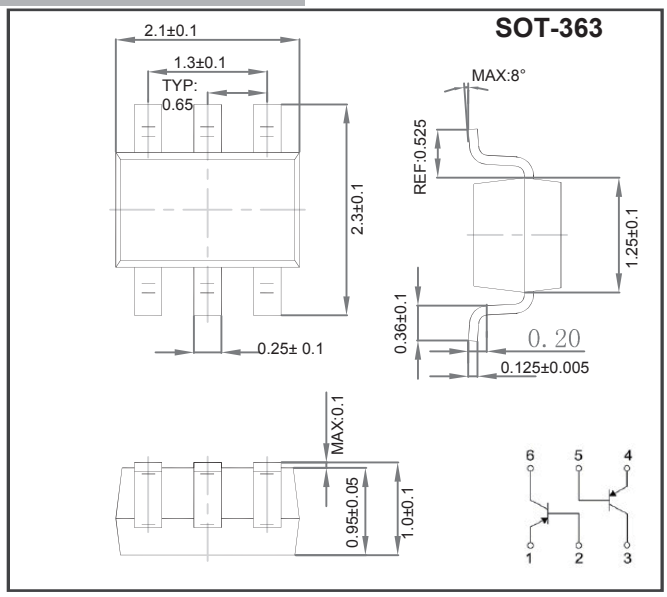
SOT-363 Plastic-Encapsulate Transistors

Features

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the rransistors

MECHANICAL DATA

- Case style:SOT-363 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-65	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current-Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature	Tstg	-55-+150	℃
Thermal resistance From junction to ambient	$R_{\theta JA}$	625	℃/W

Electrical Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified).

Parameter	Symbols	Test Condition	Limits			Unit
			Min		Max	
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10uA, I_E=0	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0			-15	nA
Base cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-2mA	110			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-0.5mA			-0.1	V
		I_C=-100mA, I_B=-5mA			-0.3	V
Base -emitter saturation voltage	$V_{BE(sat)}$	I_C=-10mA, I_B=-0.5mA		0.7		V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA,f=100MHz	100			MHz
Collector output capacitance	Cob	V_{CB}=-10V, I_E=0, f=1MHz			2.5	pF

*Pulse test: pulse width≤350us,duty cycle≤2.0%

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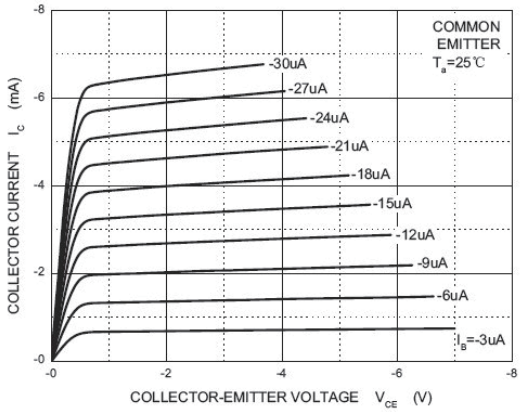
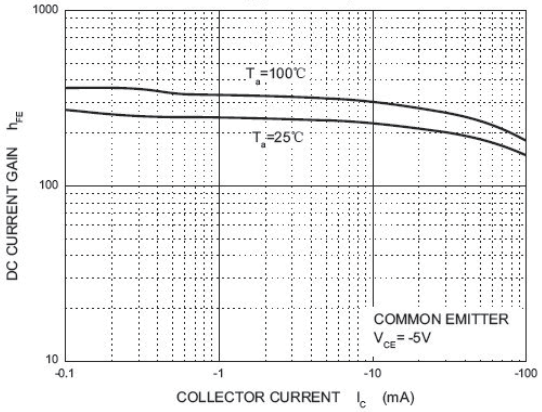
RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

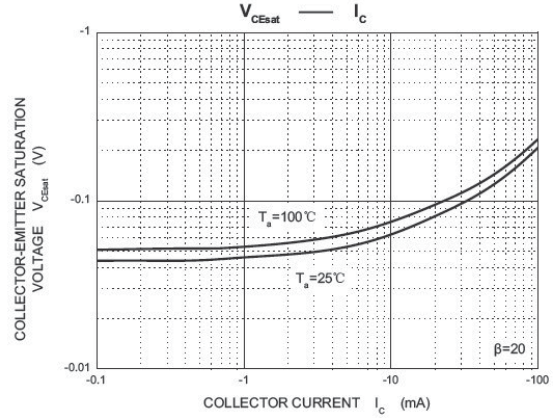
Static Characteristic



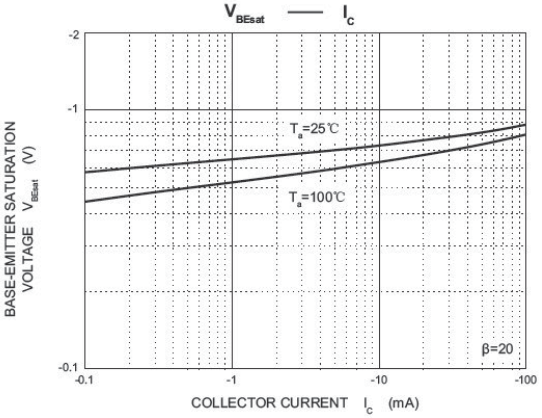
h_{FE} — I_C



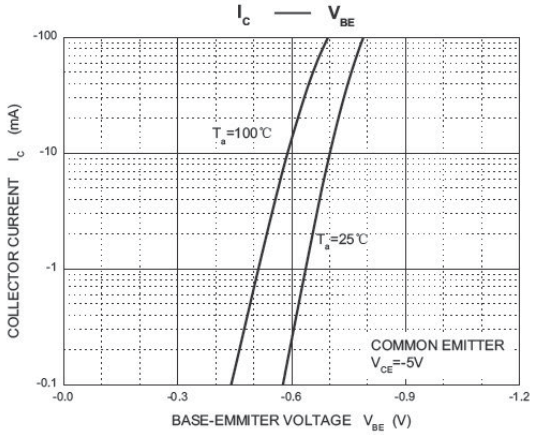
V_{CEsat} — I_C



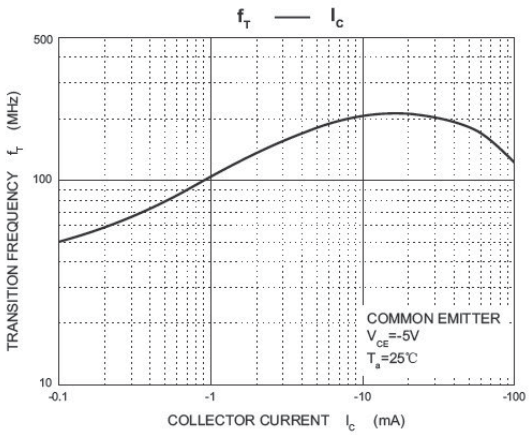
V_{BEsat} — I_C



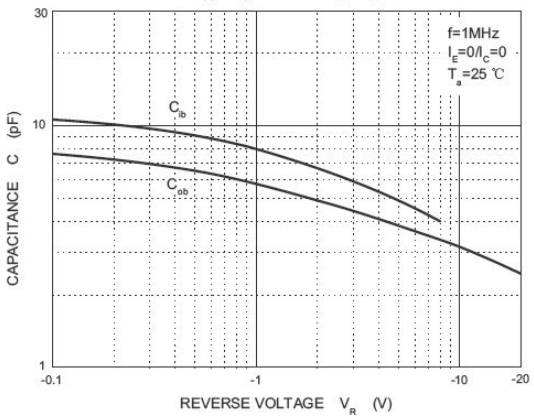
I_C — V_{BE}



f_T — I_C



C_{ob}/ C_{ib} — V_{CB}/ V_{EB}



P_C — T_a